

# 2N5064

Rev.E Mar.-2016

## 描述 / Descriptions

TO-92 塑封封装单向可控硅。Thyristor in a TO-92 Plastic Package.

## 特征 / Features

灵敏的控制级触发电流和很低的维持电流。

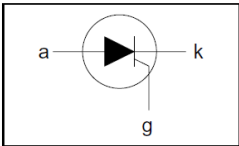
Sensitive gate trigger current and Low Holding current.

## 用途 / Applications

用作一般的开关和相位控制。

Intended for use in general purpose switching and phase control applications.

## 内部等效电路 / Equivalent Circuit



## 引脚排列 / Pinning



PIN1: Anode

PIN 2: Gate

PIN 3: Cathode

## 放大及印章代码 / $h_{FE}$ Classifications & Marking

见印章说明。See Marking Instructions.

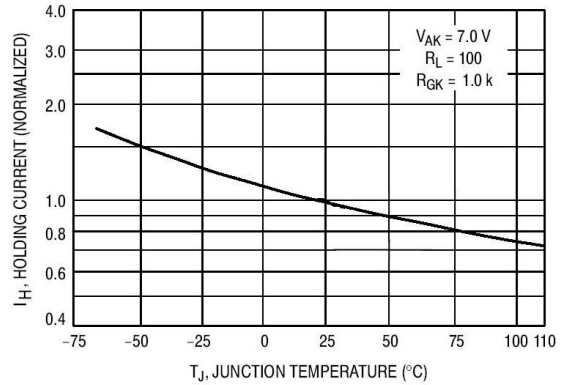
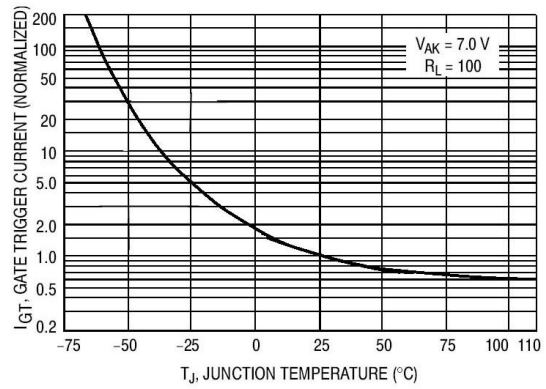
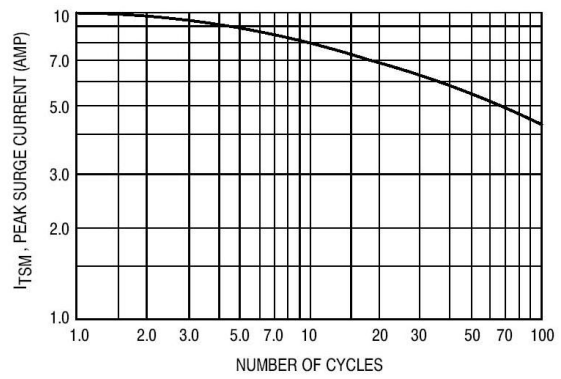
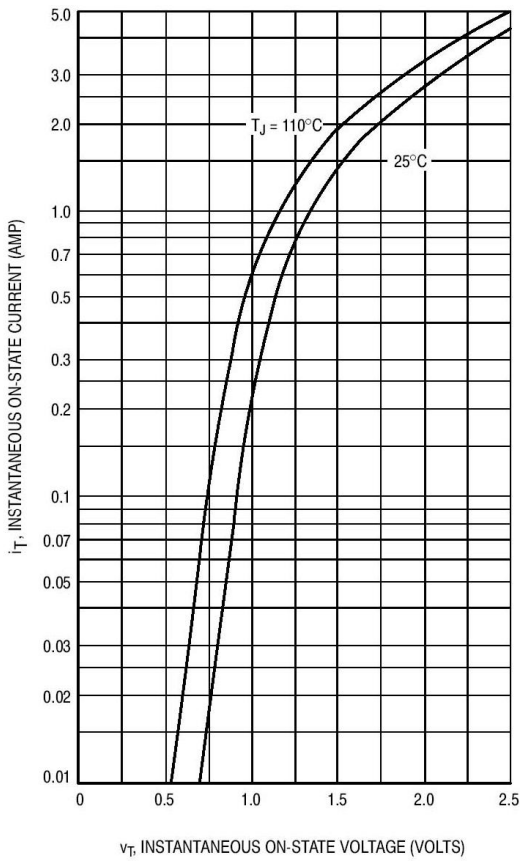
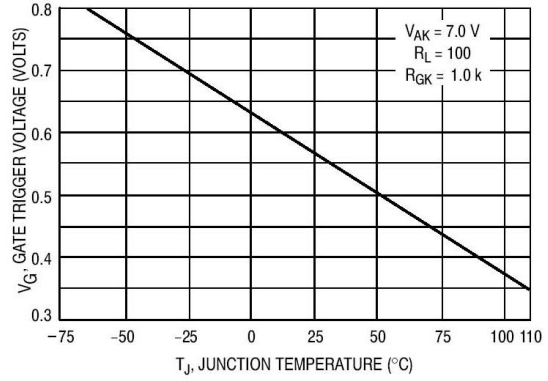
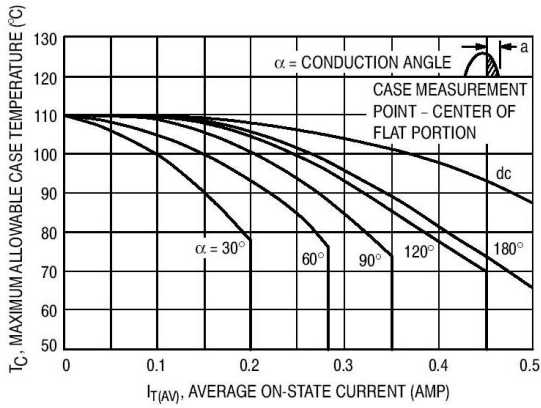
**极限参数 / Absolute Maximum Ratings(Ta=25°C)**

参数 Parameter	符号 Symbol	测试条件 Test Conditions		数值 Rating	单位 Unit
Repetitive peak off-state voltages	$V_{DRM}$ , $V_{RRM}$			200	V
RMS on-state current	$I_{T(RMS)}$			0.8	A
Average on-state current	$I_{T(AV)}$	Half sine wave	$T_C \leq 67^\circ\text{C}$	0.51	A
			$T_C \leq 102^\circ\text{C}$	0.255	
Repetitive peak on-state current	$I_{TRM}$			8.0	A
Non-repetitive peak on-state current	$I_{TSM}$	$T_a \leq 25^\circ\text{C}$	$t = 8.3\text{ms}$	10	A
$I_t^2$ for fusing	$I^2t$	$t = 8.3\text{ms}$		0.4	$\text{A}^2\text{S}$
Peak gate current	$I_{GM}$	$T_a = 25^\circ\text{C}$	$t_p = 300\mu\text{s}$ , $f = 120\text{Hz}$	1	A
Peak gate power	$P_{GM}$	$T_a = 25^\circ\text{C}$		0.1	W
Junction Temperature	$T_j$			-65~125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$			-65~150	$^\circ\text{C}$

**电性能参数 / Electrical Characteristics(Ta=25°C)**

参数 Parameter	符号 Symbol	测试条件 Test Conditions		最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Gate trigger current	$I_{GT}$	$V_D = V_{DRM(max)}$ $R_L = 100\Omega$ gate open circuit	$T_C = 25^\circ\text{C}$			200	$\mu\text{A}$
			$T_C = -65^\circ\text{C}$			350	
Latching current	$I_L$	$V_D = 12\text{V}$	$R_{GK} = 1\text{K}\Omega$			6.0	mA
Holding current	$I_H$	$V_D = 12\text{V}$	$R_{GK} = 1\text{K}\Omega$			5.0	mA
On-state voltage	$V_T$	$I_T = 1.2\text{A peak } t_p = 300\mu\text{s} \quad \delta \leq 0.01$				1.7	V
Gate trigger voltage	$V_{GT}$	$V_D = V_{DRM(max)}$ $R_L = 100\Omega$ ; gate open circuit	$T_C = 25^\circ\text{C}$			0.8	V
			$T_C = -65^\circ\text{C}$			1.2	
			$T_C = 125^\circ\text{C}$	0.1			
Off-state leakage current	$I_D, I_R$	$V_D = V_{DRM(max)}$ $V_R = V_{RRM(max)}$	$T_C = 25^\circ\text{C}$			10	$\mu\text{A}$
			$T_C = 125^\circ\text{C}$			50	
Critical rate of rise of off-state voltage	$dv/dt$	$T_C = 25^\circ\text{C} \quad T_j = 125^\circ\text{C}$ $V_{DM} = 67\% V_{DRM(max)}$ $R_{GK} = 1\text{K}\Omega$ exponential waveform			25		V/us

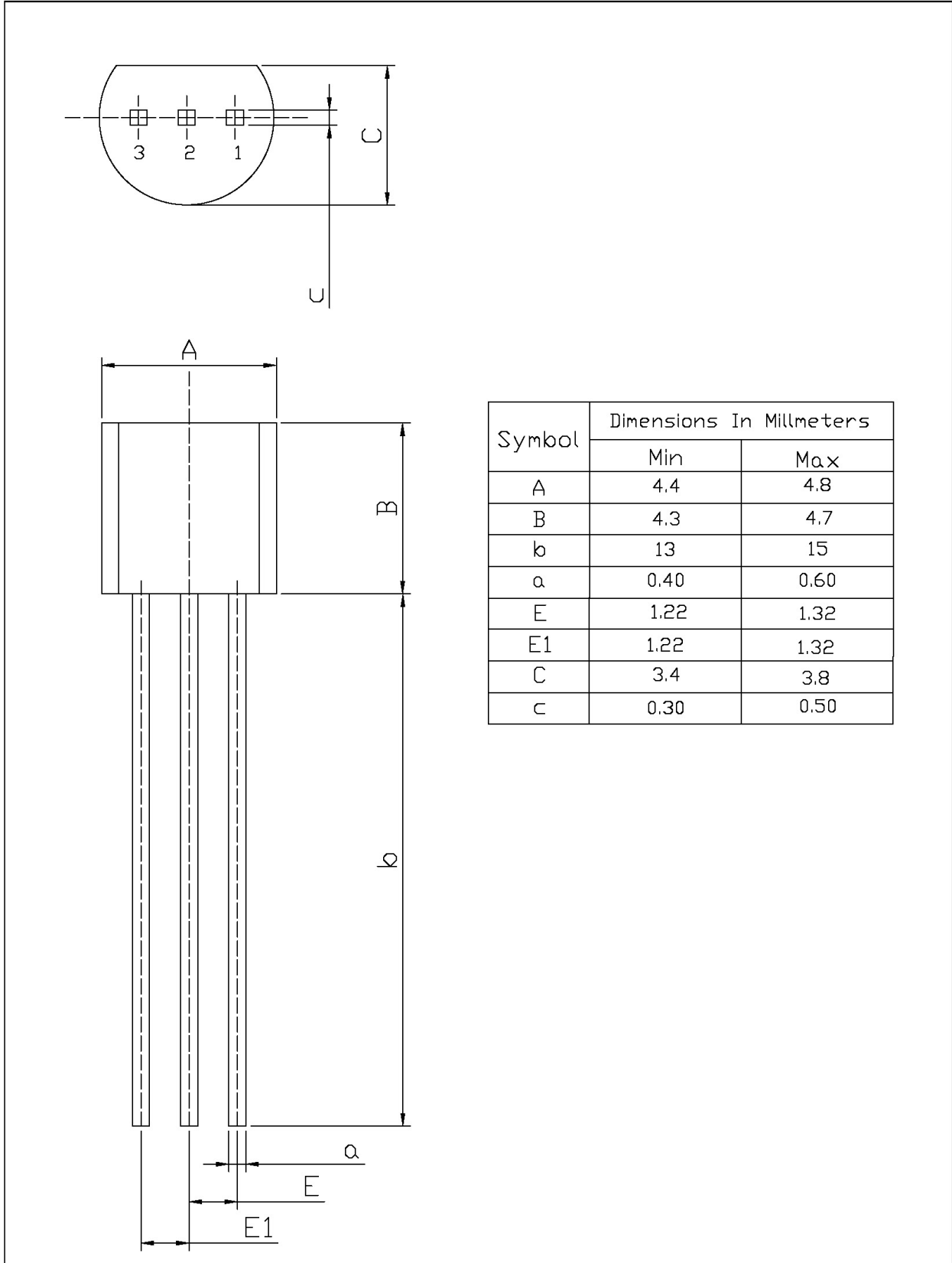
电参数曲线图 / Electrical Characteristic Curve



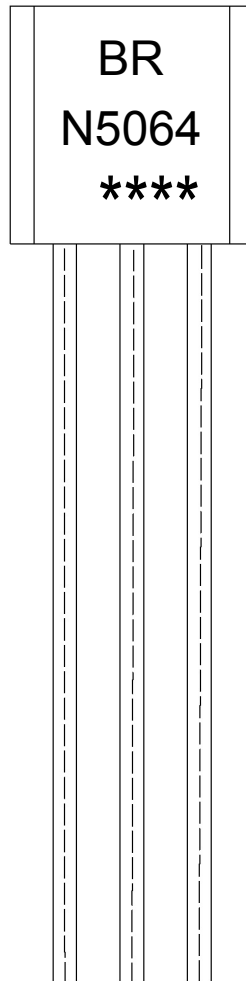
外形尺寸图 / Package Dimensions

TO-92

Unit: mm



印章说明 / Marking Instructions



说明：

BR： 为公司代码

N5064： 为型号代码

\*\*\*\*： 为生产批号代码，随生产批号变化。

Note:

BR: Company Code.

N5064: Product Type.

\*\*\*\*: Lot No. Code, code change with Lot No.

**波峰焊温度曲线图(无铅) / Temperature Profile for Dip Soldering(Pb-Free)**



说明：

- 1、预热温度 25 ~ 150°C，时间 60 ~ 90sec;
- 2、峰值温度 255±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2 ~ 10°C/sec.

Note:

- 1.Preheating:25~150°C, Time:60~90sec.
- 2.Peak Temp.:255±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

**耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions**

温度：270±5°C

时间：10±1 sec.

Temp.:270±5°C

Time:10±1 sec

**包装规格 / Packaging SPEC.**

散件包装 / BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)		
	Units/Bag 只/袋	Bags/Inner Box 袋/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Bag 袋	Inner Box 盒	Outer Box 箱
TO-92	1,000	10	10,000	5	50,000	135×190	237×172×102	560×245×195
	1,000	10	10,000	10	100,000	135×190	237×172×102	560×245×375

编带包装 / AMMO

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)	
	Units/tape 只/纸带	Tape/Inner Box 纸带/盒	Rows/Inner Box 纸带层/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Inner Box 盒	Outer Box 箱
TO-92	3,000	1	120	10	30,000	328×230×42	小箱 480×346×235, 大箱 547×407×268

**使用说明 / Notices**